



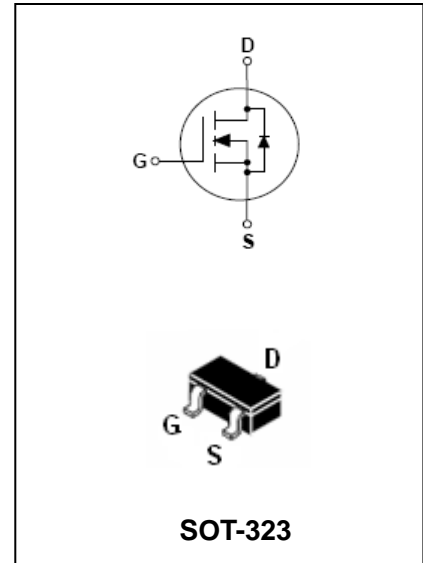
FEATURES

- High Density Cell Design For Low $R_{DS(ON)}$
- Voltage Controlled Small Signal Switch
- Rugged and Reliable
- High Saturation Current Capability
- MSL 1

APPLICATIONS

- N-channel enhancement mode effect transistor
- Switching application

ORDERING INFORMATION



Type No.	Marking	Package Code
2N7002W	7002	SOT-323

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source voltage	60	V
V_{DGR}	Drain-Gate voltage($R_{GS} \leq 1\text{M}\Omega$)	60	V
V_{GSS}	Gate -Source voltage - continuous - Non Repetitive ($t_p < 50\mu\text{s}$)	± 20 ± 40	V
I_D	Maximum Drain current -continuous -Pulsed	115 800	mA
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal resistance, Junction-to-Ambient	625	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Junction and Storage Temperature	-50 to +150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	2	
Gate-body Leakage	I_{GSS}	Forward $V_{DS}=0V, V_{GS}=20V$	-	-	1	uA
		Reverse $V_{DS}=0V, V_{GS}=-20V$	-	-	-1	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	uA
		$V_{DS}=60V, V_{GS}=0V, T_j=125^\circ C$	-	-	500	
Drain-Source on-voltage	$V_{DS(ON)}$	$V_{GS}=10V, I_D=500mA$	-	0.6	3.75	V
		$V_{GS}=5V, I_D=50mA$	-	0.09	1.5	
Forward transconductance	g_{FS}	$V_{DS}=10, I_D=200mA$	80	-	-	mS
Static drain-Source on-resistance	$R_{DS(ON)}$	$V_{GS}=5.0V, I_D=50mA$	-	3.2	7.5	Ω
		$V_{GS}=10V, I_D=500mA, T_j=100^\circ C$	-	4.4	13.5	
Drain-Source diode forward voltage	V_{SD}	$V_{GS}=0V, I_S=115mA$	-	0.88	1.5	V
Input capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$	-	20	50	pF
Output capacitance	C_{OSS}		-	11	25	
Reverse transfer capacitance	C_{RSS}		-	4	5	
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 30V, I_D= 0.2A,$ $R_L = 150\Omega, V_{GS}= 10V,$ $R_{GEN}= 25\Omega$	-	-	20	ns
Turn-Off Delay Time	$t_{D(OFF)}$		-	-	20	ns



TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

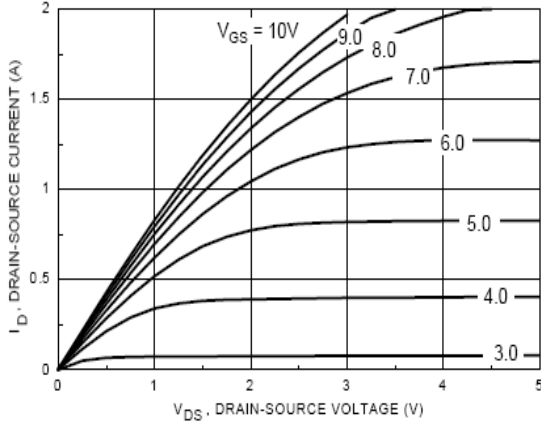


Figure 1. On-Region Characteristics

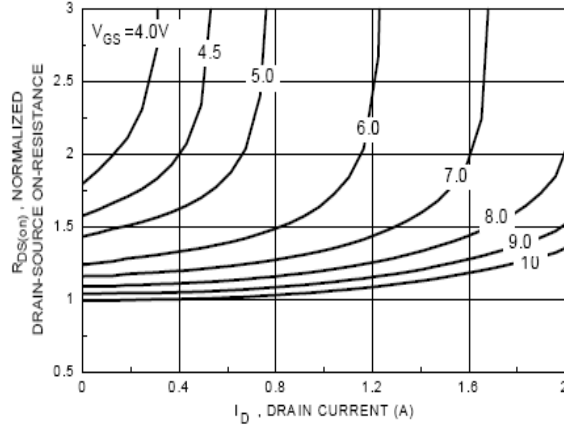


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

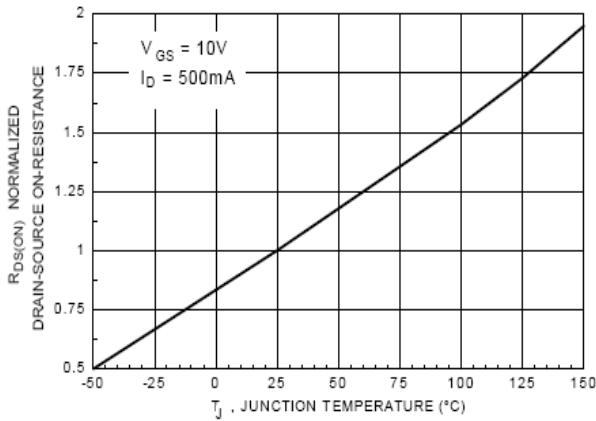


Figure 3. On-Resistance Variation with Temperature

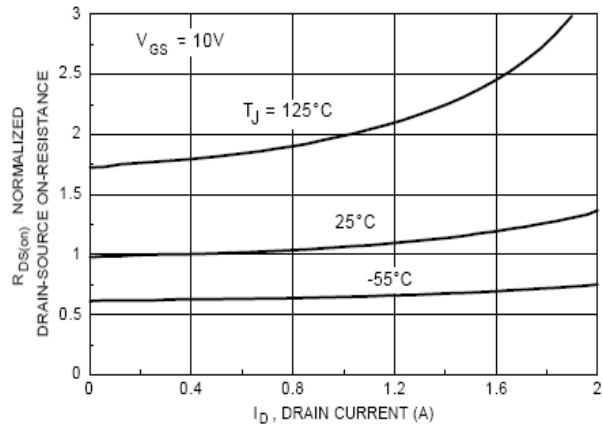


Figure 4. On-Resistance Variation with Drain Current and Temperature

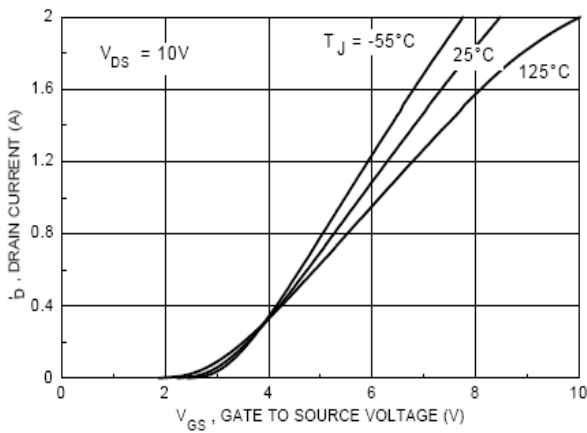


Figure 5. Transfer Characteristics

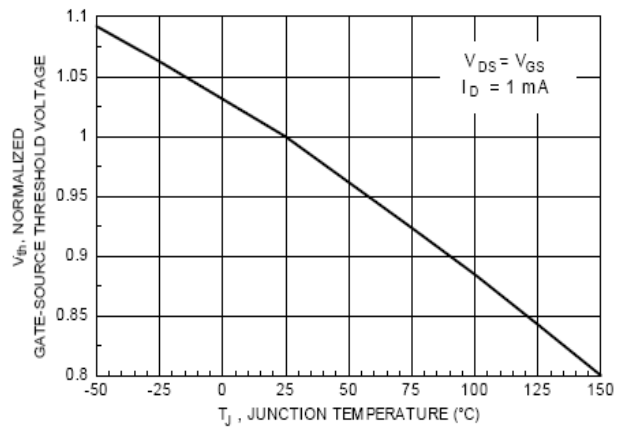


Figure 6. Gate Threshold Variation with Temperature

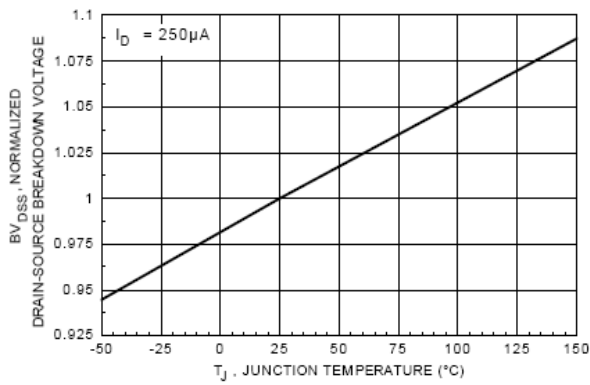


Figure 7. Breakdown Voltage Variation with Temperature

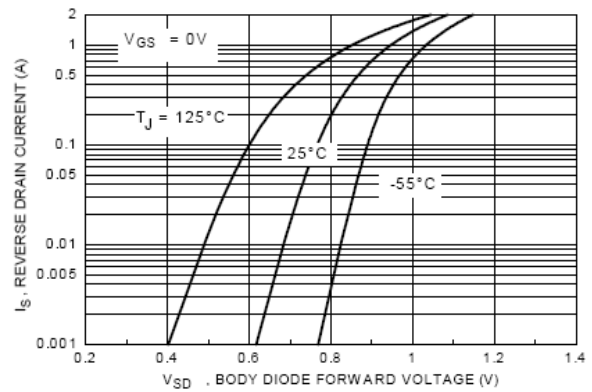
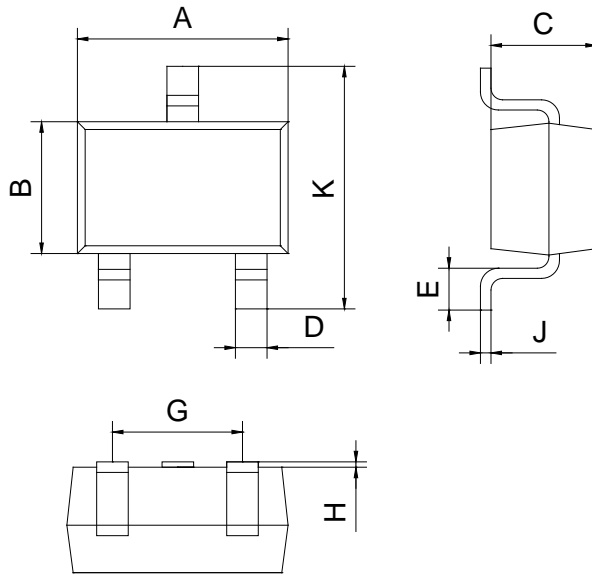


Figure 8. Body Diode Forward Voltage Variation with Temperature

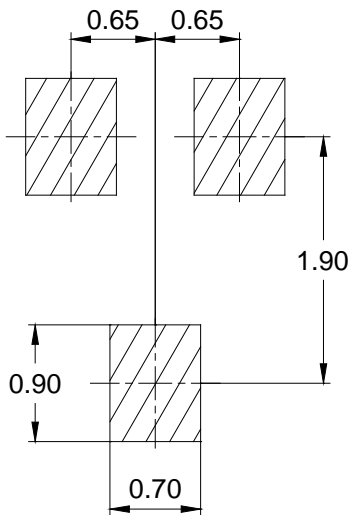


PACKAGE OUTLINE



SOT-323		
Dim	Min	Max
A	2.00	2.20
B	1.15	1.35
C	0.90	1.10
D	0.15	0.35
E	0.25	0.40
G	1.20	1.40
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit: mm

PACKAGE INFORMATION

Device	Package	Shipping
2N7002W	SOT-323	3000 pcs / Tape & Reel